Electrical Characteristics of the IGBT

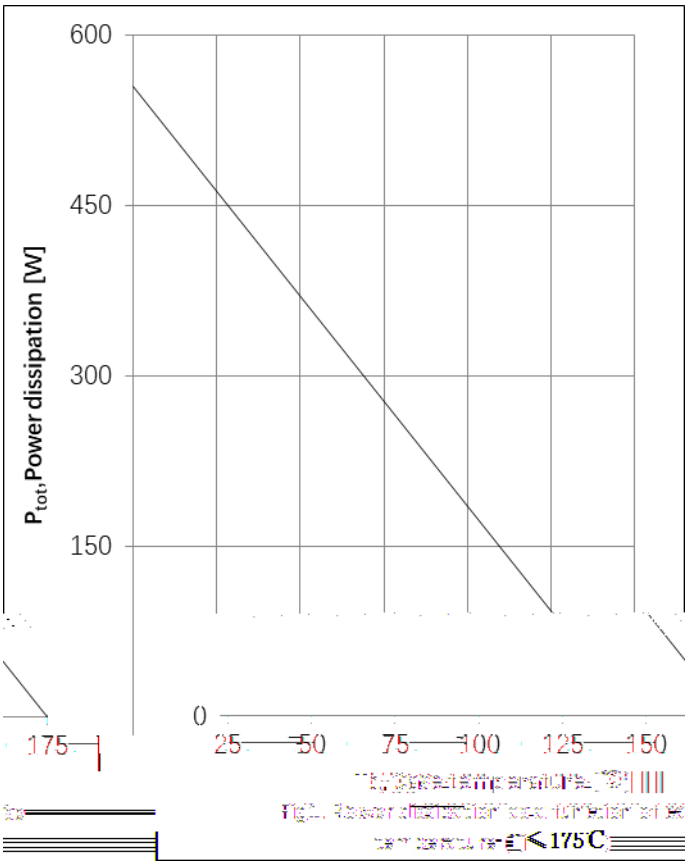
Electrical Characteristics of the Diode T_j= 25 u.2 84i.2 84less o.2 84therwise sp.2 84ecified

Parameter	Sy.2 84mb	Co.2 84i.20(d.2 8		Ty.2 84	Mx.2 8	Ui.2584
Static						

Dio.221(d.221(e)] TJETQ

Electrical Characteristics of the DIODE

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at T_j= 25						
Reverse Recovery Current	I_{rr}	I_F=75A, V_R=600V, di/dt= -500	-	9	-	A
Diode reverse recovery time	trr		-	268	-	ns
Reverse Recovery Charge	Q_{rr}		-	3.42	-	uC



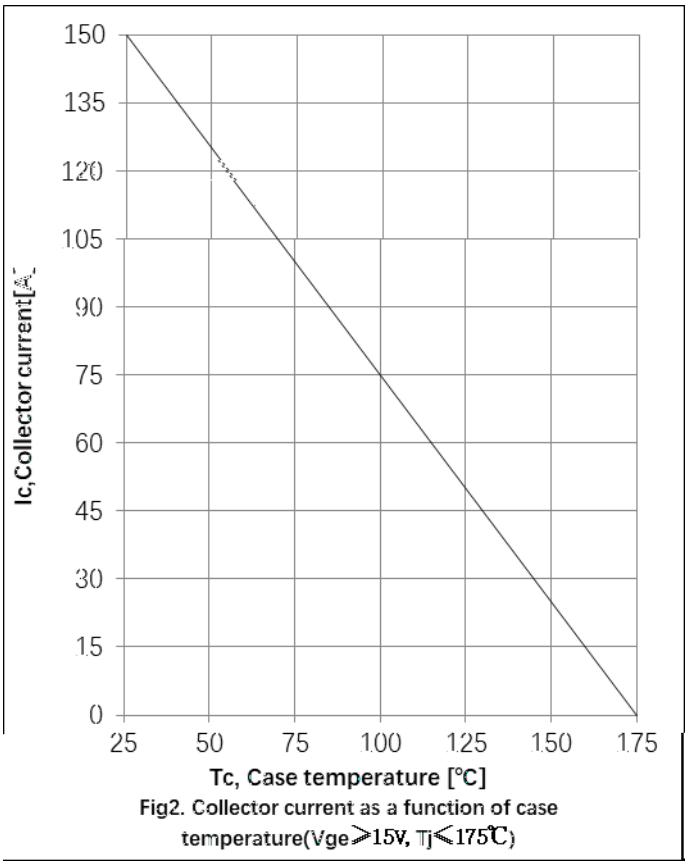
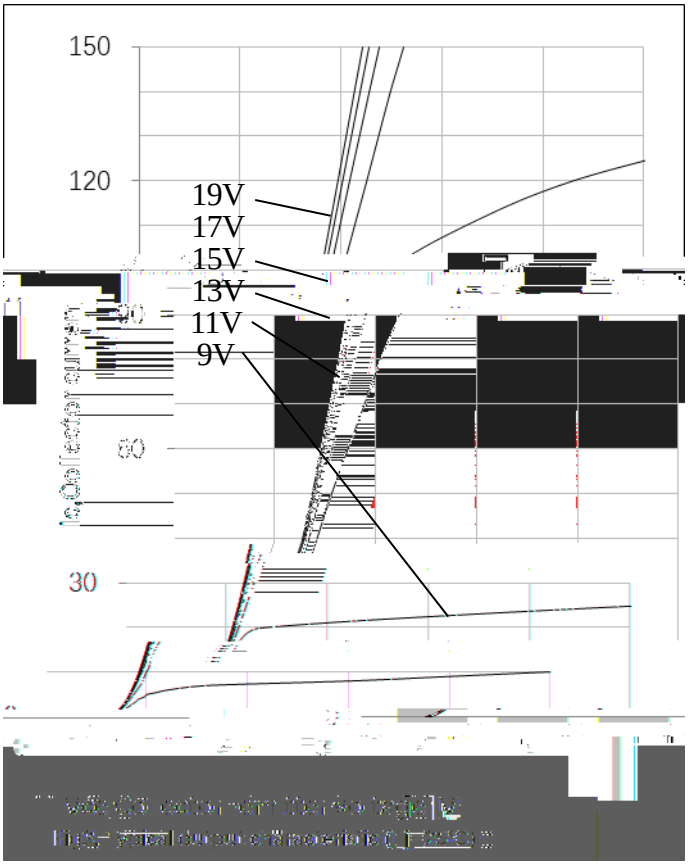
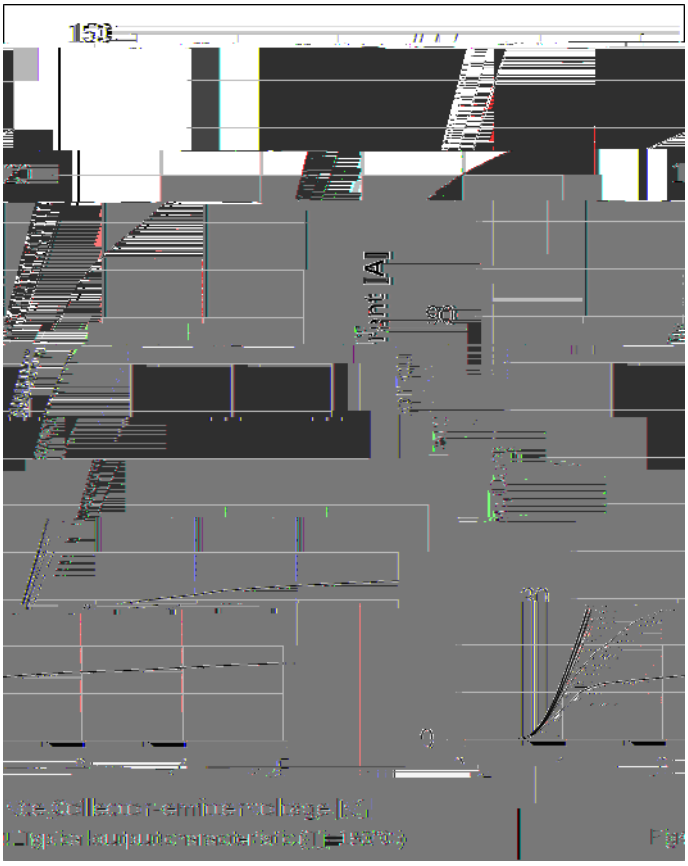
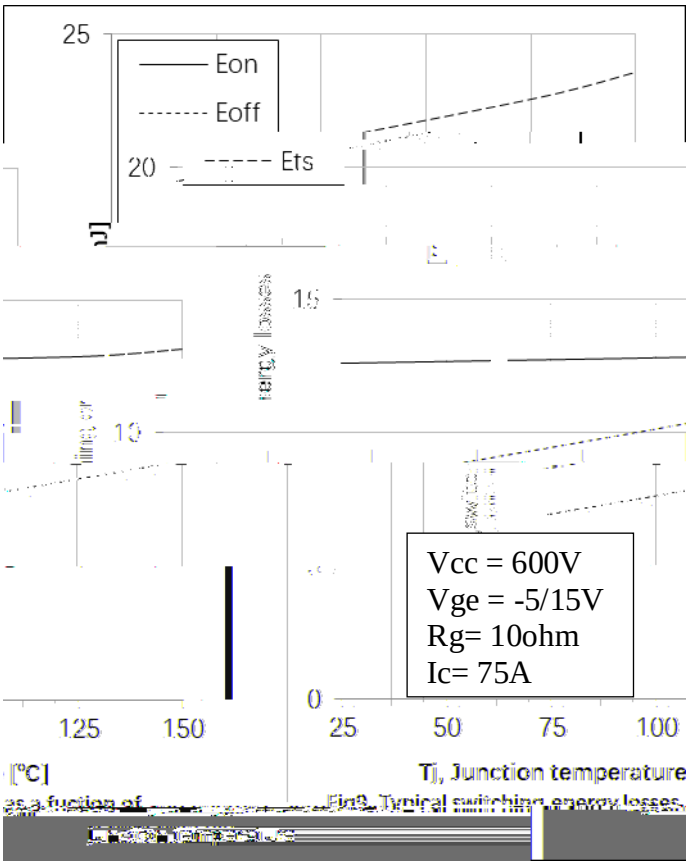
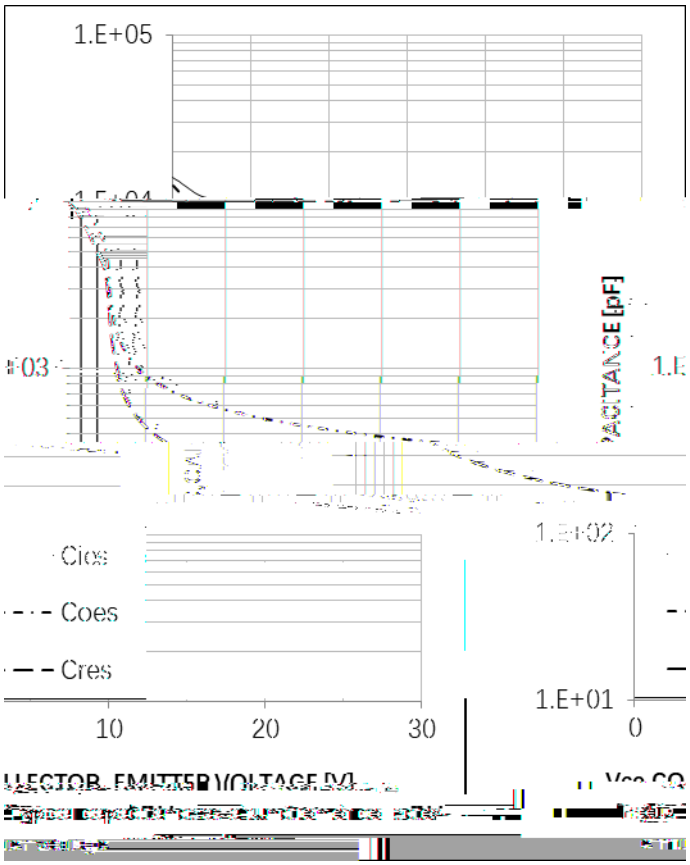


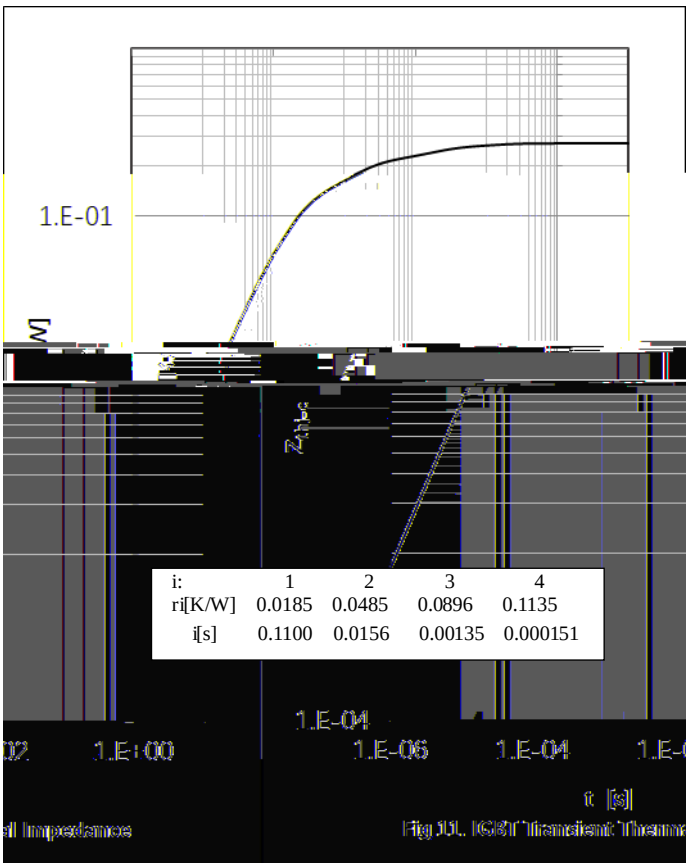
Fig2. Collector current as a function of case temperature(Vge≥15V, Tj≤175℃)

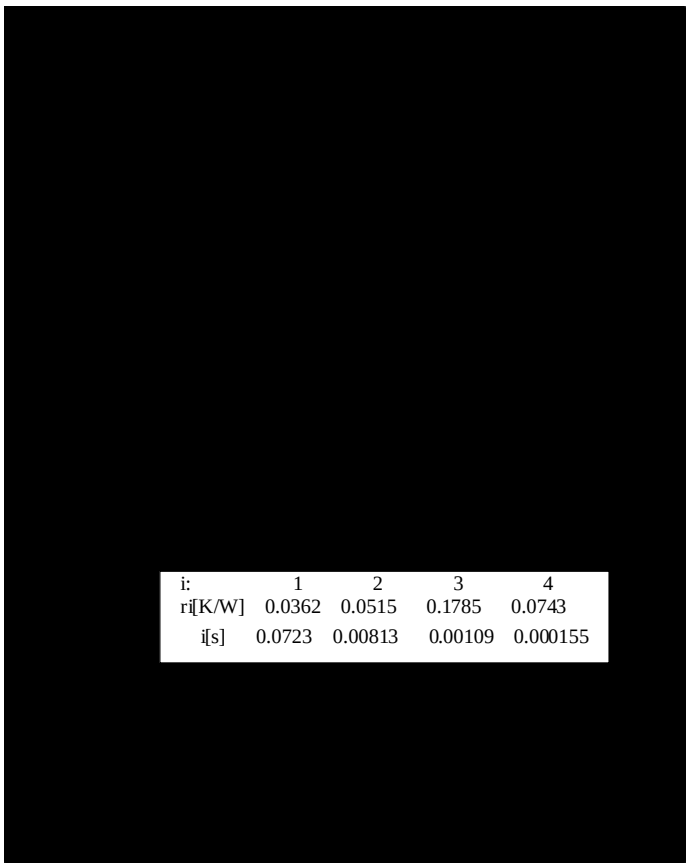





Eon
Eoff
Ets
Vcc = 600V
Vge = -5/15V
Rg= 10ohm
Ic= 75A
Tj, Junction temperature


Cies
Coes
Cres


i: 1 2 3 4
ri[K/W] 0.0185 0.0485 0.0896 0.1135
i[s] 0.1100 0.0156 0.00135 0.000151


i: 1 2 3 4
ri[K/W] 0.0362 0.0515 0.1785 0.0743
i[s] 0.0723 0.00813 0.00109 0.000155

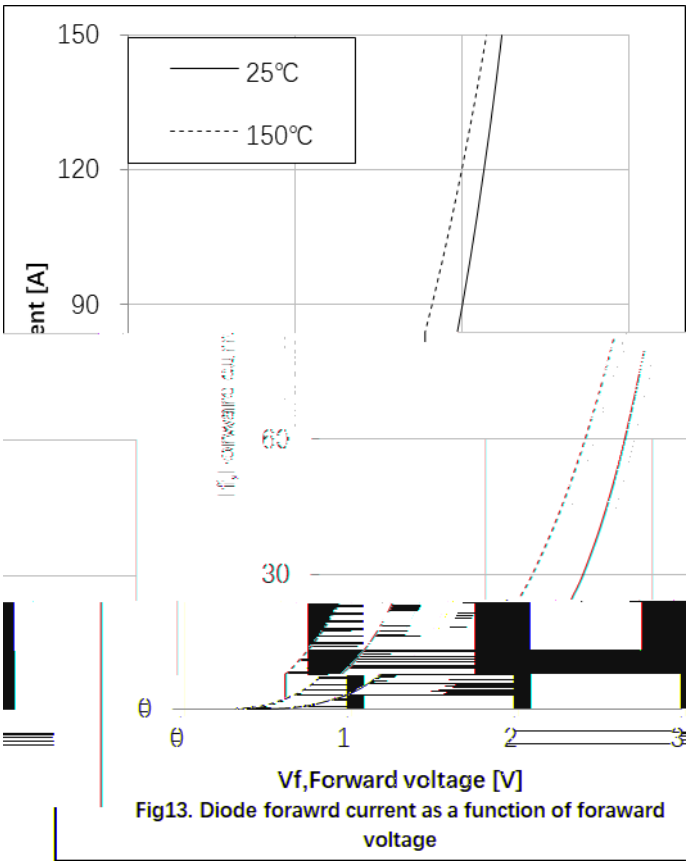
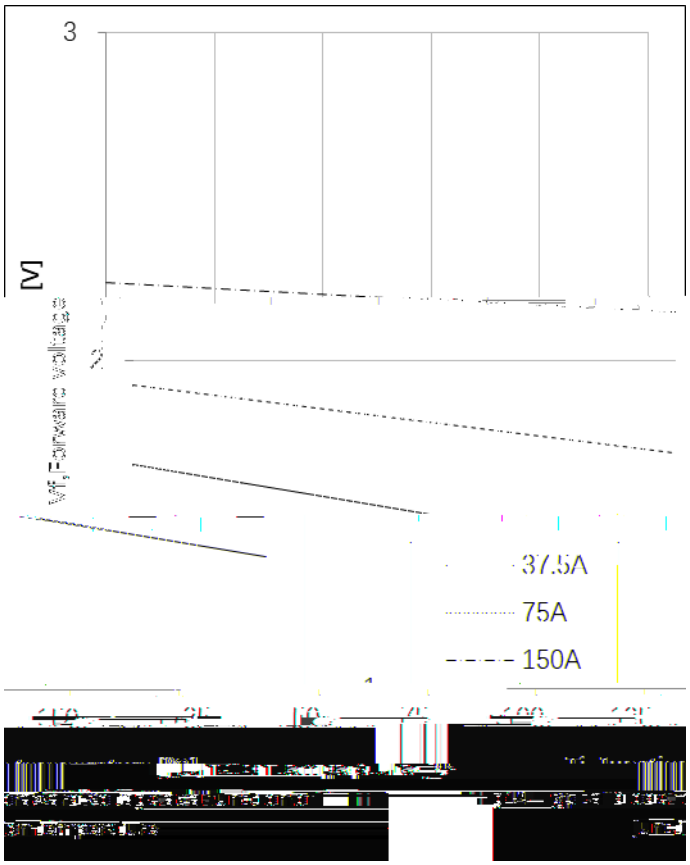


Fig13. Diode forawrd current as a function of foraward voltage



DGL75N120CTL1J